

DERWENT-ACC-NO: 1992-067414

DERWENT-WEEK: 199951

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TITLE: Thin-film FET for memory - has source and
drain electrodes buried in insulation film between
upper gate electrode and film covering lower electrode
NoAbstract Dwg 1/9

PATENT-ASSIGNEE: CASIO COMPUTER CO LTD [CASK]

PRIORITY-DATA: 1990JP-0092021 (April 9, 1990)

PATENT-FAMILY:

PUB-NO	MAIN-IPC	PUB-DATE	LANGUAGE
PAGES JP 03290970 A 005	N/A	December 20, 1991	N/A
JP <u>2969184</u> B2 009	H01L 027/115	November 2, 1999	N/A

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
APPL-DATE JP 03290970A April 9, 1990	N/A	1990JP-0092021
JP 2969184B2 April 9, 1990	N/A	1990JP-0092021
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ABSTRACTED-PUB-NO: JP 2969184B

EQUIVALENT-ABSTRACTS:

Optical disk having a resin substrate has a trench on the periphery when the resin substrates are adhered to each other. A groove or pit for tracking is formed on a side of a resin substrate. A 1st ceramics layer, a

recording layer, 2nd ceramics layer and a reflection layer are laminated in order. The plates are adhered using epoxy gp. resin. A trench is formed at the periphery and a UV curing type resin is filled into the trench. The resin is cured and the periphery is cut.

ADVANTAGE - No change of mechanical characteristics at higher temp..

TITLE-TERMS: THIN FILM PET MEMORY SOURCE DRAIN ELECTRODE BURY INSULATE FILM

UPPER GATE ELECTRODE FILM COVER LOWER ELECTRODE
NOABSTRACT

DERWENT-CLASS: U11 U12 U13 U14

EPI-CODES: U11-C18B5; U12-B03A; U12-D02A1; U12-Q; U13-C04B2; U14-A03B7;

U14-H01A,

SECONDARY-ACC-NO:

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